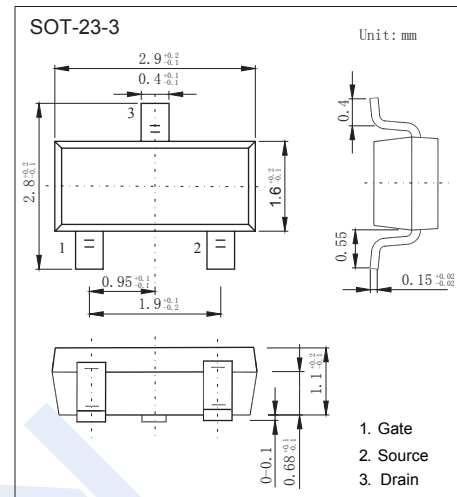
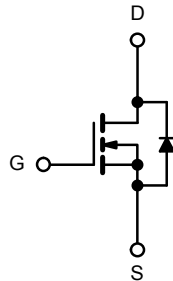


## N-Channel MOSFET

### SI2318CDS (KI2318CDS)

#### ■ Features

- $V_{DS} (V) = 40V$
- $I_D = 5.6 A (V_{GS} = 10V)$
- $R_{DS(ON)} < 42m\Omega (V_{GS} = 10V)$
- $R_{DS(ON)} < 51m\Omega (V_{GS} = 4.5V)$



#### ■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current	$I_D$	$T_c=25^\circ C$	A
		$T_c=70^\circ C$	
		$T_a=25^\circ C$	
		$T_a=70^\circ C$	
Pulsed Drain Current	$I_{DM}$	20	
Power Dissipation	$P_D$	$T_c=25^\circ C$	W
		$T_c=70^\circ C$	
		$T_a=25^\circ C$	
		$T_a=70^\circ C$	
Thermal Resistance.Junction- to-Ambient	$R_{thJA}$	100	$^\circ C/W$
Thermal Resistance.Junction- to-Foot	$R_{thJF}$	60	
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55 to 150	

## N-Channel MOSFET

### SI2318CDS (KI2318CDS)

#### ■ Electrical Characteristics Ta = 25°C

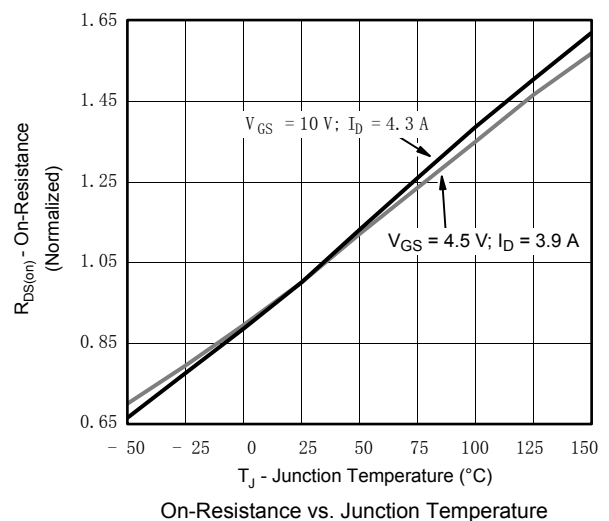
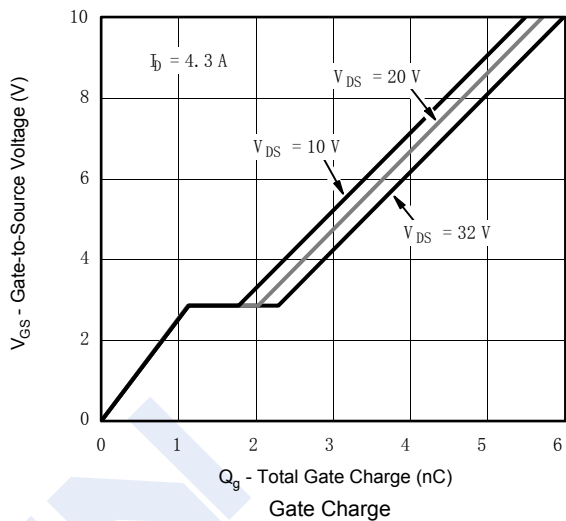
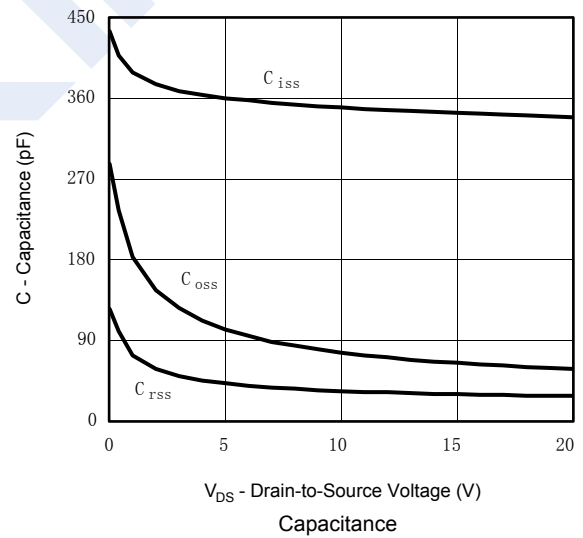
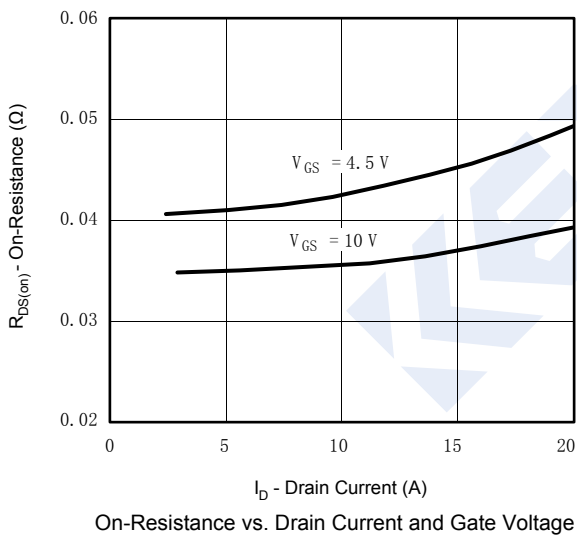
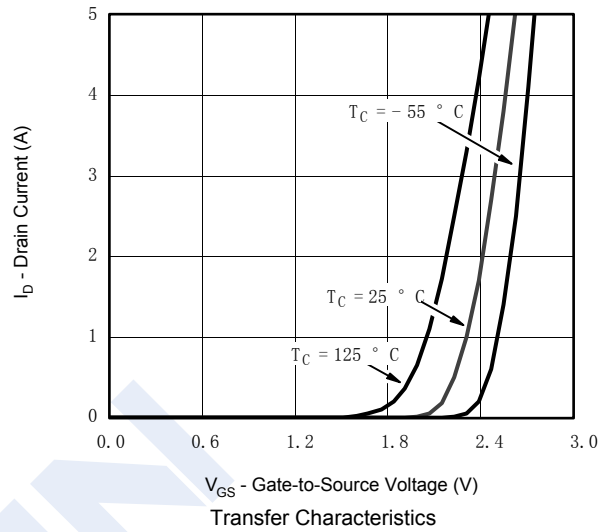
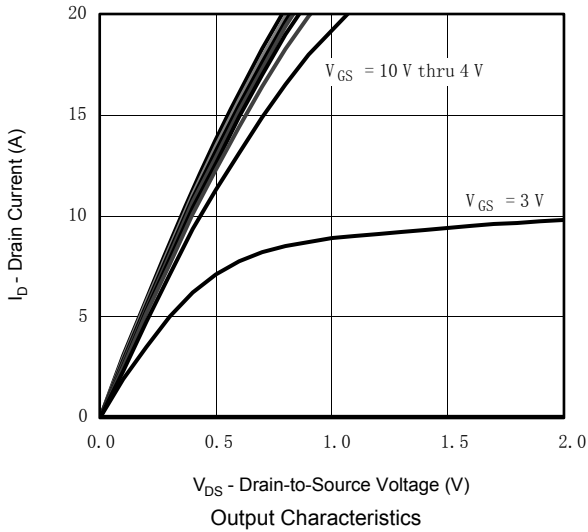
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V <sub>DSS</sub>	I <sub>D</sub> =250 μA, V <sub>GS</sub> =0V	40			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V			1	μA
		V <sub>DS</sub> =40V, V <sub>GS</sub> =0V, T <sub>J</sub> =70°C			10	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.2		2.5	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =4.3A			42	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3.9A			51	
On State Drain Current	I <sub>D(ON)</sub>	V <sub>DS</sub> ≥5V, V <sub>GS</sub> =10V	20			A
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =20V, I <sub>D</sub> =4.3A		17		S
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =20V, f=1MHz		340		pF
Output Capacitance	C <sub>oss</sub>			60		
Reverse Transfer Capacitance	C <sub>rss</sub>			30		
Gate Resistance	R <sub>g</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	0.6		6.6	Ω
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =20V, V <sub>DS</sub> =10V, I <sub>D</sub> =4.3A		5.8	9	nC
		V <sub>GS</sub> =20V, V <sub>DS</sub> =4.5V, I <sub>D</sub> =4.3A		2.9	6	
Gate Source Charge	Q <sub>gs</sub>	V <sub>GS</sub> =20V, V <sub>DS</sub> =4.5V, I <sub>D</sub> =4.3A		1.1		
Gate Drain Charge	Q <sub>gd</sub>			0.9		
Turn-On DelayTime	t <sub>d(on)</sub>	V <sub>DD</sub> = 20V, R <sub>L</sub> = 5.7Ω I <sub>D</sub> =3.5A, V <sub>GEN</sub> = 4.5V, R <sub>G</sub> = 1Ω		12	20	ns
Turn-On Rise Time	t <sub>r</sub>			50	75	
Turn-Off DelayTime	t <sub>d(off)</sub>			10	20	
Turn-Off Fall Time	t <sub>f</sub>			8	16	
Turn-On DelayTime	t <sub>d(on)</sub>	V <sub>DD</sub> = 20V, R <sub>L</sub> = 5.7Ω I <sub>D</sub> =3.5A, V <sub>GEN</sub> = 10V, R <sub>G</sub> = 1Ω		7	14	ns
Turn-On Rise Time	t <sub>r</sub>			20	30	
Turn-Off DelayTime	t <sub>d(off)</sub>			14	21	
Turn-Off Fall Time	t <sub>f</sub>			8	16	
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =3.5A, di/dt=100A/μs, T <sub>J</sub> =25°C		15	23	nC
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			7	14	
Reverse Recovery Fall Time	t <sub>a</sub>			11		ns
Reverse Recovery Rise Time	t <sub>b</sub>			4		
Maximum Body-Diode Continuous Current	I <sub>S</sub>	T <sub>C</sub> =25°C			1.75	A
Pulse Diode Forward Current	I <sub>SM</sub>				20	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =3.5A, V <sub>GS</sub> =0V			1.2	V

#### ■ Marking

Marking	P9*
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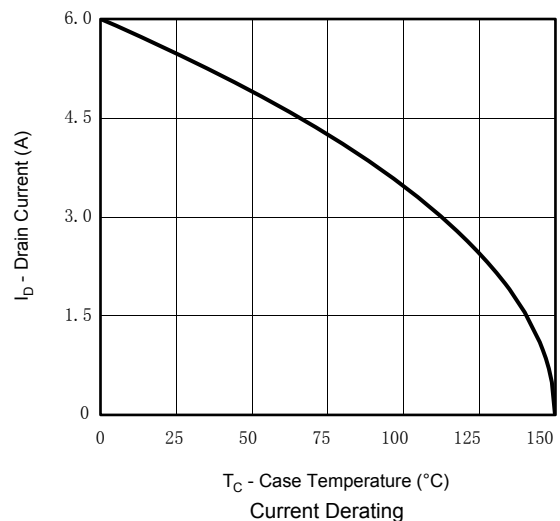
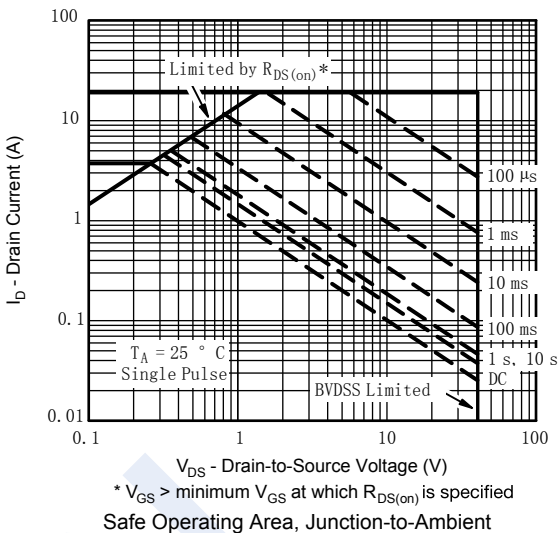
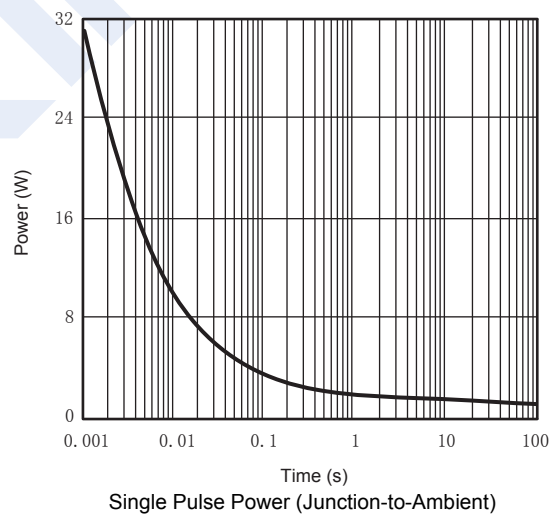
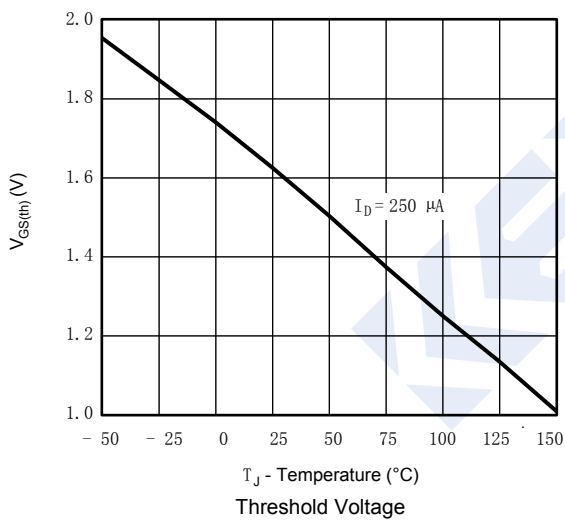
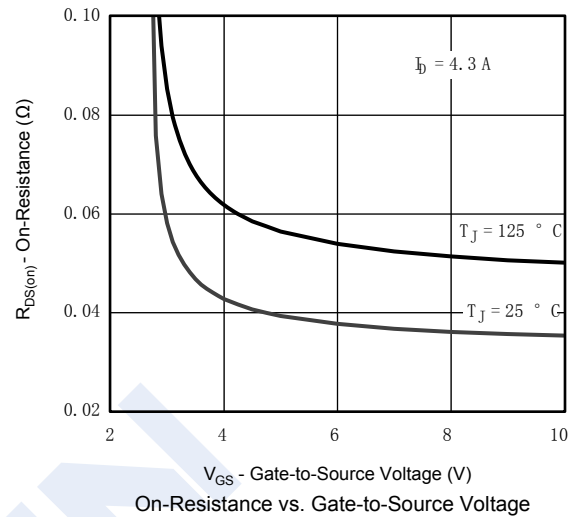
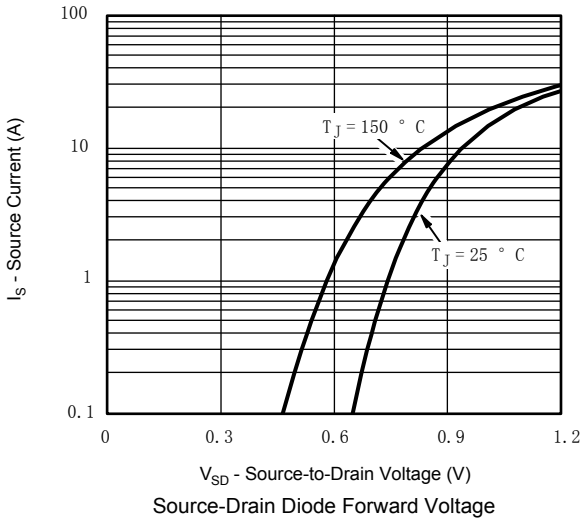
## N-Channel MOSFET SI2318CDS (KI2318CDS)

■ Typical Characteristics



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■ Typical Characteristics



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■ Typical Characteristics

